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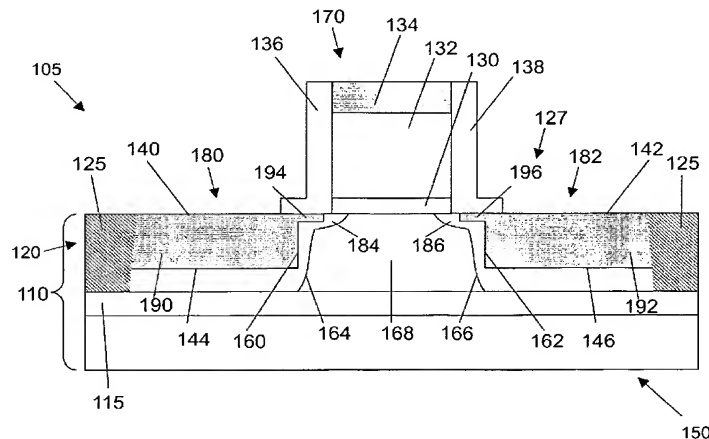
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[Continued on next page]

(54) Title: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE



(57) Abstract: This invention relates to a semiconductor device (105) and a method of manufacturing this device. A preferred embodiment of the invention is a semiconductor device (105) comprising a silicon semiconductor substrate (110), an oxide layer (115) and an active layer (120). In the active layer, insulating areas (125) and an active area (127) have been formed. The active area (127) comprises a source (180), a drain (182) and a body (168). The source (180) and drain (182) also comprise source and drain extensions (184, 186). The active layer (120) is provided with a gate (170). On both sides of the gate (170), L-shaped side wall spacers are located. The source (180) and drain (182) also comprise silicide regions (190, 192). A characteristic of these regions is that they have extensions (194, 196) located under the side wall spacers (136, 138). These extensions (194, 196) strongly reduce the series resistance of the source (194) and drain (196), which significantly improves the performance of the semiconductor device (105).

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